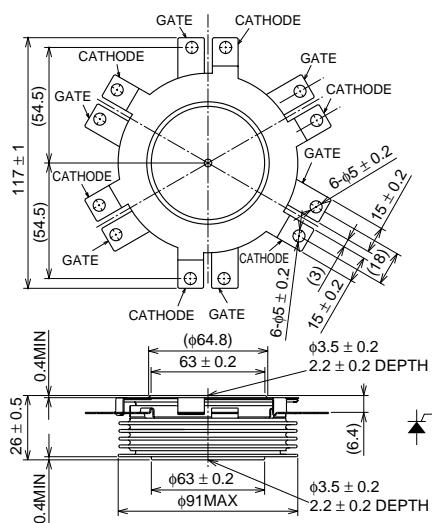


FGC1500A-130DSHIGH POWER INVERTER USE
PRESS PACK TYPE**FGC1500A-130DS**

- Symmetrical GCT
- ITQRM Repetitive controllable on-state current 1500A
- IT(AV) Average on-state current 500A
- VDRM Repetitive peak off-state voltage 6500V
- VRM Repetitive peak reverse voltage 6500V

OUTLINE DRAWING

Dimensions in mm

**APPLICATION**

Current source inverters, DC choppers, Induction heaters, DC to DC converters.

MAXIMUM RATINGS

Symbol	Parameter	Conditions	Voltage class	Unit
VRM	Repetitive peak reverse voltage	—	6500	V
VRSM	Non-repetitive peak reverse voltage	—	6500	V
VDRM	Repetitive peak off-state voltage	VGK = -2V	6500	V
VDSM	Non-repetitive peak off-state voltage	VGK = -2V	6500	V
VLTDS	Long term DC stability voltage	VGK = -2V, λ = 100 Fit	3600	V

Symbol	Parameter	Conditions	Ratings	Unit
ITQRM	Repetitive controllable on-state current	VDM = 3/4 VDRM, VD = 3000V, LC = 0.3μH, VRG = 20V Tj = 25/115°C, diga/dt= 2250A/μs (see Fig. 1, 3)	1500	A
IT(RMS)	RMS on-state current	Applied for all conduction angles	780	A
IT(AV)	Average on-state current	f = 60Hz, sinewave θ = 180°, Tf = 55°C	500	A
ITSM	Surge on-state current		8	kA
I ² t	Current-squared, time integration	One half cycle at 60Hz, Tj = 115°C Start	2.7 × 10 ⁵	A ² s
diT/dt	Critical rate of rise of on-state current	Vd = 3000V, It = 1500A, Cs= 0.2μF, RS= 5Ω, Tj = 25/115°C f = 60Hz, IGM = 90A, dig/dt= 50A/μs (see Fig. 1, 2.)	1000	A/μs
VFGM	Peak forward gate voltage		10	V
VRGM	Peak reverse gate voltage		21	V
IFGM	Peak forward gate current		900	A
IRGM	Peak reverse gate current		1500	A
PFGM	Peak forward gate power dissipation		9	kW
PRGM	Peak reverse gate power dissipation		32	kW
PFG(AV)	Average forward gate power dissipation		180	W
PRG(AV)	Average reverse gate power dissipation		230	W
Tj	Junction temperature		-20 ~ +115	°C
Tsg	Storage temperature		-20 ~ +150	°C
—	Mounting force required	(Recommended value 20kN)	18 ~ 24	kN
—	Weight	Typical value	760	g

Mar. 2002

FGC1500A-130DSHIGH POWER INVERTER USE
PRESS PACK TYPE**ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{TM}	On-state voltage	I _T = 1500A, T _j = 115°C	—	—	7.0	V
I _{IRRM}	Repetitive peak reverse current	V _{RM} = 6500V, T _j = 115°C	—	—	220	mA
I _{IDRM}	Repetitive peak off-state current	V _{DM} = 6500V, V _{GK} = -2V, T _j = 115°C	—	—	150	mA
I _{IGRM}	Reverse gate current	V _{RG} = 21V, T _j = 115°C	—	—	100	mA
dV/dt	Critical rate of rise of off-state voltage	V _D = 3000V, V _{GK} = -2V, T _j = 115°C (Expo. wave)	3000	—	—	V/μs
t _{gt}	Turn-on time	I _T = 1500A, V _D = 3000V, dI/dt = 1000A/μs, T _j = 115°C Cs = 0.2μF, R _S = 5Ω, I _{GM} = 90A, dI _G /dt = 50A/μs (see Fig. 1, 2)	—	—	5.0	μs
t _d	Delay time		—	—	1.0	μs
E _{on}	Turn-on switching energy		—	—	2.15	J/P
t _s	Storage time	I _T = 1500A, V _{DM} = 3/4 V _{DRM} , V _D = 3000V Cs = 0.2μF, R _S = 5Ω, V _{RG} = 20V, T _j = 115°C dI _{GQ} /dt = 2250A/μs (see Fig. 1, 5)	—	—	3.0	μs
E _{off}	Turn-off switching energy		—	—	12	J/P
Q _{RR}	Reverse recovery charge	V _R = 3000V, I _T = 1500A, dI/dt = 1000A/μs Cs = 0.2μF, R _S = 5Ω, T _j = 115°C (see Fig. 4, 5)	—	—	2800	μC
E _{rec}	Reverse recovery energy		—	—	7	J/P
I _{GT}	Gate trigger current	DC METHOD : V _D = 24V, R _L = 0.1Ω, T _j = 25°C	—	—	0.75	A
V _{GT}	Gate trigger voltage		—	—	1.5	V
R _{th(j-f)}	Thermal resistance	Junction to fin	—	—	0.016	K/W

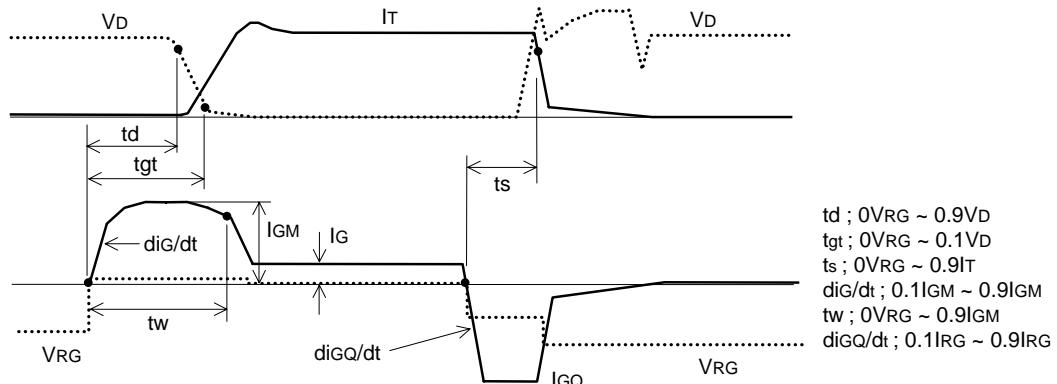


Fig. 1 Turn-on and Turn-off waveform

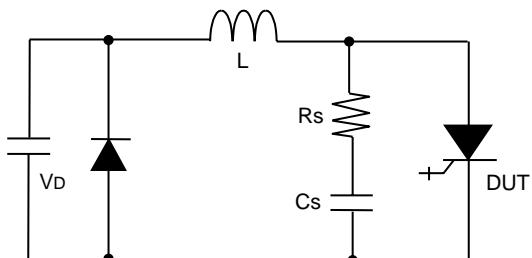


Fig. 2 Turn-on test circuit

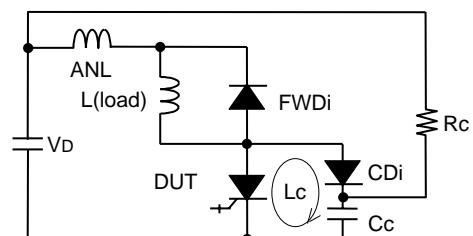
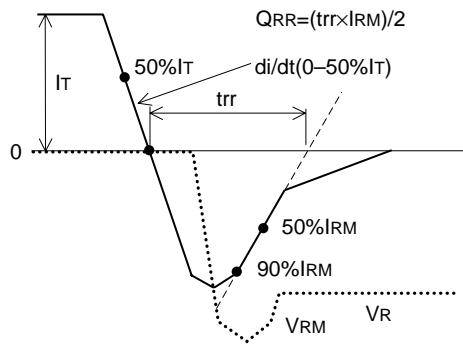
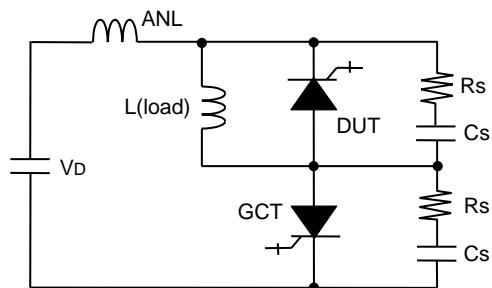
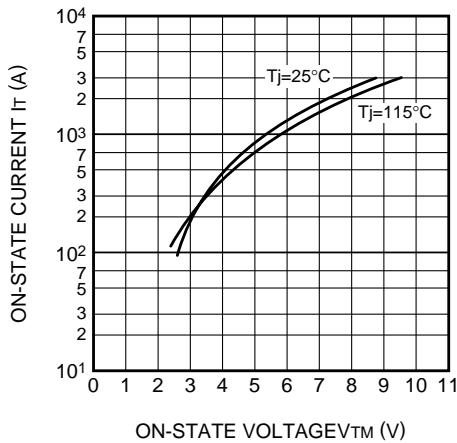
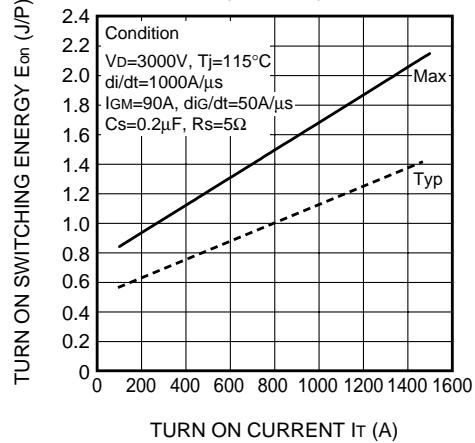
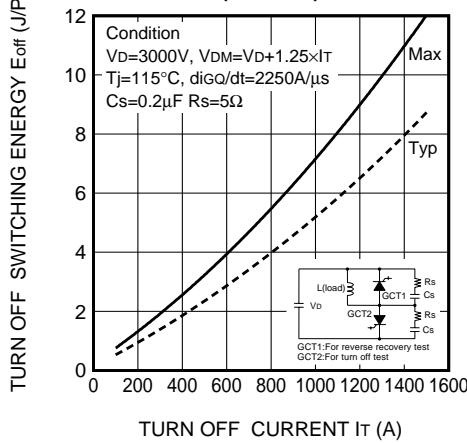
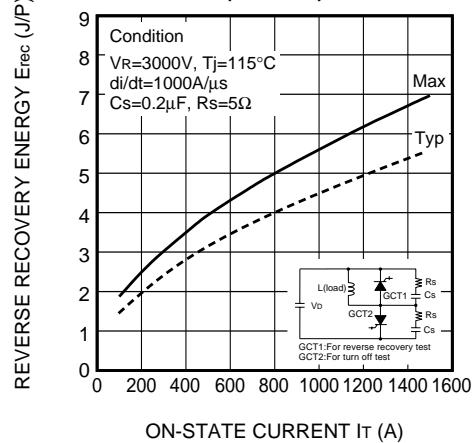
Fig. 3 Turn-off test circuit
(With clamp circuit)

Fig. 4 Reverse recovery waveform

Fig. 5 Turn-off and Reverse recovery test circuit
(With CR snubber circuit)

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTIC

E_{on} VS IT
(TYPICAL)E_{off} VS IT
(TYPICAL)E_{rec} VS IT
(TYPICAL)MAXIMUM THERMAL IMPEDANCE
CHARACTERISTIC
(JUNCTION TO FIN)